

The 21st Korean Conference on Semiconductors
제21회 한국반도체학술대회
February 24–26, 2014 / Hanyang University, Seoul, Korea

C. Materials Growth & Characterization 분과

[WD3-C] Growth of Single Crystalline Semiconductor

Date	Feb. 26, 2014 (Wed.)
Place	Room D / 제1공학관 402호 (# 402, Engineering Building I)

Session Chair: 권순용 교수(UNIST), 박진섭 교수(한양대학교)

- WD3-C-1 15:50-16:05 Single Crystalline Ge Heteroepitaxy on Hastelloy Substrate via Laser-Induced Melting and Solidification**
저자: Yong-Hoon Son, Sangsoo Lee, and Euijoon Yoon
소속: Department of Materials Science and Engineering, Seoul National University
- WD3-C-2 16:05-16:20 Seed Shape Dependence of Ingot Crystalline Characteristics in Single-Crystal Sapphire Ingot Grown by Kyropoulos Method**
저자: Jun-Seong Park, Il-Hwan Kim, Gon-Sub Lee, and Jea-Gun Park
소속: Department of Electronics and Communication Engineering, Hanyang University
- WD3-C-3 16:20-16:35 Strained Si:C Epi 층에서 Dopant 가 Carbon 고용도에 미치는 영향 분석**
저자: Taeone Youn¹, Taekwon Lee¹, Jaegeun Oh², Juhee Lee¹, Sujin Kong¹, Won Kim¹, and Hojoung Kim¹
소속: ¹Analysis Team, SK hynix Inc., ²NMProcess S-Team, SK hynix Inc.
- WD3-C-4 16:35-16:50 Plasma Enhanced Atomic Layer Deposition of Low Temperature Silicon Oxide using New Cyclodisilazane Structure Precursors**
저자: 김성기, 양병일, 장세진, 김종현, 김도연, 조성우, 석장현, 이상익, 김명운
소속: (주)디엔에프